Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	2	((ground) and (buried adj layer) and (shield$4) and (dop$3)).clm.	US-PGPUB	OR	OFF	2005/12/05 11:44

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4813	257/774,778.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/05 11:23
L2	3657	257/774,778.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/05 11:25
L3	2	((ground) and (buried adj layer) and (shield$4) and (dop$3)).clm.	US-PGPUB	OR	OFF	2005/12/05 11:44
L4	1	("0538121").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/05 11:44
L5	0	("0538121").PN.	JPO	OR	OFF	2005/12/05 11:44
L6	1	("11068029").PN.	JPO	OR	OFF	2005/12/05 11:46
L7	0	("6064508").PN.	JPO	OR	OFF	2005/12/05 11:46
L8	1	("11354563").PN.	JPO	OR	OFF	2005/12/05 11:46
L9	0	("5992558").PN.	JPO	OR	OFF	2005/12/05 11:46
L10	0	"538121"	JPO	OR	OFF	2005/12/05 11:47
L11	0	"538121.pt."	JPO	OR	OFF	2005/12/05 11:47
L12	0	"538121.pt"	JPO	OR	OFF	2005/12/05 11:47
L13	0	"538121.pt."	JPO	OR	OFF	2005/12/05 11:48
L14	0	53-8121	JPO	OR	OFF	2005/12/05 11:48
L15	0	("53-8121").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/05 11:48
S1	86013	radio adj frequency	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/14 14:34
S2	180	radio adj frequency adj component	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/14 14:43

S3	1220	(257/690).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/14 17:50
S4	651	(257/727).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/14 16:06
S5	539	(257/728).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/14 16:07
S6	1163	(257/700).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/14 18:40
S7	235	(257/660).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/14 19:22
S8	753	(257/659).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/14 18:06
S9	397	((chip with substrate) with (conductive adj layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/14 21:12
S10	15	((chip with substrate) with ((conductive adj layer) near1 chip))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/14 19:25
S11	98	((conductive adj layer) near chip)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/14 19:49

S12	0	((conductive adj layer adj (inside)) near chip)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/14 19:33
S13	1406	((conductive adj layer) with chip)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/14 19:49
S14	0	((conductive adj layer adj in) with chip)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/14 19:50
S15	1	((((buried near conductive) adj layer) near (conductive adj layer)) with chip)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/14 19:52
S16	17	((buried near conductive) with chip)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/14 19:53
S17	369	((chip with substrate) with (conductive adj layer))	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/14 21:52
S18	267	(chip adj (contact or contacts)) with (conductive)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/14 21:53
S19	359	(chip adj (contact or contacts)) with (conductive or conductor)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/14 22:33
S20	384870	chip	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/14 22:34
S21	49285	chip with substrate	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/14 22:35
S22	8779	S8/$.ccls. and (chip with substrate)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/14 22:35

S23	2037	S8/$.ccls. and (chip near substrate)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/14 22:38
S24	24605	((substrate with (contacts)))	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/14 22:39
S25	8	(substrate near (buried near conductive near layer))	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/14 22:53
S26	2392	(substrate near ((mono$1crystalline) adj (silicon)))	USPAT	OR	OFF	2002/09/14 22:54
S27	1160	S8/$.ccls. and (substrate near ((mono$1crystalline) adj (silicon)))	USPAT	OR	OFF	2002/09/14 23:10
S28	3	S8/$.ccls. and ((substrate near ((mono$1crystalline) adj (silicon))) with (advantage))	USPAT	OR	OFF	2002/09/14 22:57
S29	5	((substrate near ((mono$1crystalline) adj (silicon))) with (advantage))	USPAT	OR	OFF	2002/09/14 22:58
S30	0	((substrate near ((mono$1crystalline) adj (silicon))) with (advantage))	JPO	OR	OFF	2002/09/14 22:59
S31	9	S8/$.ccls. and (substrate near ((mono$1crystalline) adj (silicon)))	JPO	OR	OFF	2002/09/14 22:59
S32	5	S8/$.ccls. and (substrate with ((mono$1crystalline) adj (silicon))) with advantage	USPAT	OR	OFF	2002/09/14 23:10
S34	159	"257"/$.ccls. and (faraday adj cage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/06 10:53
S35	2	"257"/$.ccls. and (faraday adj cage) and (ground with buried)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/06 10:57
S36	14	(faraday adj cage) and (ground with buried)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/06 10:55
S37	320675	"257"/$.ccls. (ground with buried)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/06 10:57

S38	723	"257"/$.ccls. and (ground with buried)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/06 11:40
S39	39	"257"/$.ccls. and (buried adj layer) and (electro$1magnetic adj shield$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/06 11:44
S40	1095	(257/659-660).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/06 12:01
S41	11	((buried adj layer) with ground) and (electro$1magnetic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/06 12:07
S42	242	((buried adj layer) with ground)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/06 12:25
S43	13533	((buried) with ground$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/06 12:25
S44	292	((buried adj layer) with ground$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/06 12:26
S45	573	((buried adj layer) same ground$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/06 12:25
S46	51	((buried adj layer) with grounded)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/06 12:26
S47	69	((buried adj layer) with (grounded or grounding))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/06 12:26

S48	818	(257/731,673).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/04 16:38
S49	2573	(257/691,693).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/04 18:11
S50	3446	faraday adj cage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/04 16:59
S51	180	"257"/$.ccls. and faraday adj cage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/04 16:46
S52	119	"257"/$.ccls. and faraday adj cage	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/04 16:47
S53	2723	faraday adj cage	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/04 17:36
S54	2608	257/686	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/04 17:37
S55	2298	(257/691,693).CCLS.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/04 19:02
S56	1294	(257/698).CCLS.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/04 19:25
S57	1413	(257/700).CCLS.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/04 19:34
S59	0	257/774,778	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/04 19:50